

## TPS61162D Dual-Channel WLED Drivers for Smart Phones

### 1 Features

- 2.7-V to 6.5-V Input Voltage
- Integrated 1.5-A/40-V MOSFET
- 1.2-MHz Switching Frequency
- Dual Current Sinks of up to 30-mA Current Each
- 1% Typical Current Matching and Accuracy
- 26.5-V Overvoltage Protection Threshold
- Adaptive Boost Output to WLED Voltages
- Very Low Voltage Headroom Control (90 mV)
- Flexible Digital and PWM Brightness Control
- One-Wire Control Interface (EasyScale™)
- PWM Dimming Control Interface
- Up to 100:1 PWM Dimming Ratio
- Up to 10-Bit Dimming Resolution
- Up to 90% Efficiency
- Built-in Soft Start
- Built-in WLED Open and Short Protection
- Thermal Shutdown
- Supports 4.7- $\mu$ H Inductor Application

### 2 Applications

- Smart Phones
- PDAs, Handheld Computers
- GPS Receivers
- Backlight for Small and Media Form Factor LCD Display With Single-Cell Battery Input

### 3 Description

The TPS61162D is a dual-channel WLED driver which provides highly integrated solutions for single-cell Li-ion-battery-powered smart-phone backlighting. The device has a built-in high efficiency boost regulator with integrated 1.5-A/40-V power MOSFET and can support as low as 2.7-V input voltage. With two high current-matching capability current sink regulators, the device can drive up to 7s2p WLED diodes. The boost output can automatically adjust to the WLED forward voltage, allowing very low voltage headroom control, thus improving LED strings efficiency effectively.

The TPS61162D supports both the PWM dimming interface and one-wire digital EasyScale dimming interface and can realize 9-bit brightness code programming.

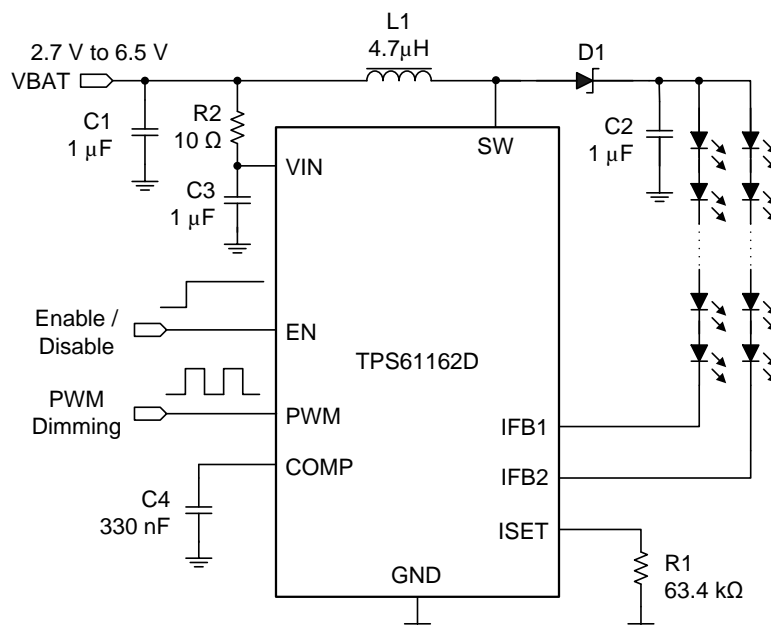
The TPS61162D integrates built-in soft start, overvoltage, and overcurrent protection, as well as thermal shutdown protections.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (MAX)
TPS61162D	DSBGA (9)	1.336 mm × 1.336 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### Typical Application



## Table of Contents

<b>1 Features</b> .....	<b>1</b>	8.3 Feature Description.....	<b>9</b>
<b>2 Applications</b> .....	<b>1</b>	8.4 Device Functional Modes.....	<b>12</b>
<b>3 Description</b> .....	<b>1</b>	8.5 Programming.....	<b>13</b>
<b>4 Revision History</b> .....	<b>2</b>	<b>9 Application and Implementation</b> .....	<b>16</b>
<b>5 Device Comparison Table</b> .....	<b>3</b>	9.1 Application Information.....	<b>16</b>
<b>6 Pin Configuration and Function</b> .....	<b>3</b>	9.2 Typical Application .....	<b>16</b>
<b>7 Specifications</b> .....	<b>4</b>	<b>10 Power Supply Recommendations</b> .....	<b>22</b>
7.1 Absolute Maximum Ratings .....	<b>4</b>	<b>11 Layout</b> .....	<b>22</b>
7.2 ESD Ratings.....	<b>4</b>	11.1 Layout Guidelines .....	<b>22</b>
7.3 Recommended Operating Conditions.....	<b>4</b>	11.2 Layout Example .....	<b>22</b>
7.4 Thermal Information .....	<b>4</b>	<b>12 Device and Documentation Support</b> .....	<b>23</b>
7.5 Electrical Characteristics.....	<b>5</b>	12.1 Device Support.....	<b>23</b>
7.6 EasyScale Timing Requirements.....	<b>6</b>	12.2 Community Resources.....	<b>23</b>
7.7 Typical Characteristics .....	<b>7</b>	12.3 Trademarks .....	<b>23</b>
<b>8 Detailed Description</b> .....	<b>8</b>	12.4 Electrostatic Discharge Caution.....	<b>23</b>
8.1 Overview .....	<b>8</b>	12.5 Glossary .....	<b>23</b>
8.2 Functional Block Diagram .....	<b>8</b>	<b>13 Mechanical, Packaging, and Orderable Information</b> .....	<b>23</b>

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Original (July 2013) to Revision A</b>	<b>Page</b>
• Added <i>Device Information</i> and <i>Pin Configuration and Functions</i> sections, <i>ESD Ratings</i> table and <i>Thermal Information</i> table with updated thermal values, <i>Feature Description</i> , <i>Device Functional Modes</i> , <i>Application and Implementation</i> , <i>Power Supply Recommendations</i> , <i>Layout</i> , <i>Device and Documentation Support</i> , and <i>Mechanical, Packaging, and Orderable Information</i> sections.....	<b>1</b>
• Changed wording of last paragraph of <i>Boost Converter</i> section.....	<b>9</b>
• Changed wording of third paragraph of <i>Overvoltage Protection</i> section .....	<b>10</b>
• Changed some of the wording of <i>PWM Control Interface</i> section .....	<b>13</b>
• Changed wording of <i>Output Capacitor Selection</i> section.....	<b>18</b>

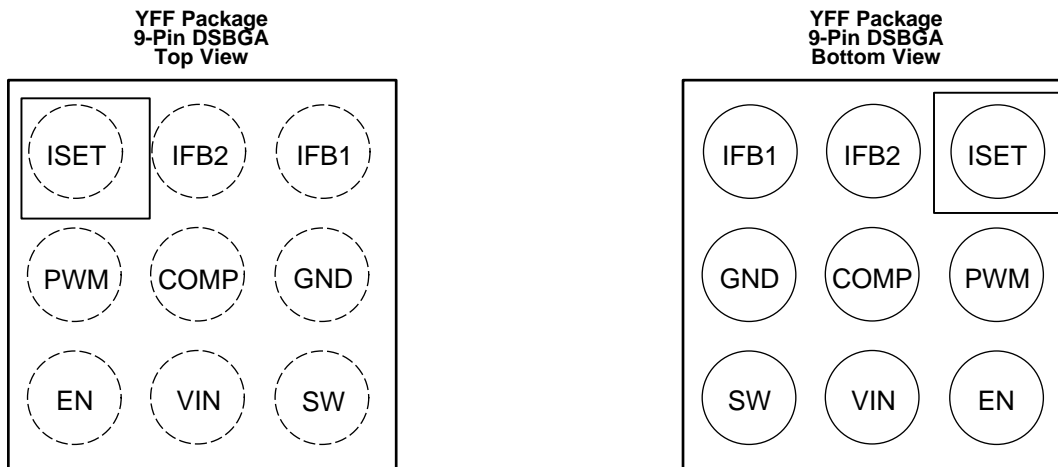
## 5 Device Comparison Table

 See<sup>(1)</sup>

T <sub>A</sub>	PART NUMBER	OPEN LED PROTECTION	PACKAGE	ORDERING	PACKAGE MARKING
–40°C to 85°C	TPS61162D	26.5 V (typical)	9-pin DSBGA	TPS61162DYFFR	TPS61162D

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at [www.ti.com](http://www.ti.com).

## 6 Pin Configuration and Function



### Pin Functions

PIN		I/O	DESCRIPTION
NUMBER	NAME		
A1	ISET	I	Full-scale LED current set pin. Connecting a resistor to the pin programs the full-scale LED current.
A2	IFB2	I	Regulated current sink input pin
A3	IFB1	I	Regulated current sink input pin
B1	PWM	I	PWM dimming signal input
B2	COMP	O	Output of the transconductance error amplifier. Connect external capacitor to this pin to compensate the boost loop.
B3	GND	O	Ground
C1	EN	I	Enable control and one-wire digital signal input
C2	VIN	I	Supply input pin
C3	SW	I	Drain connection of the internal power MOSFET

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage <sup>(2)</sup>	VIN, EN, PWM, IFB1, IFB2	−0.3	7	V
	COMP, ISET	−0.3	3	V
	SW	−0.3	40	V
Continuous power dissipation, P <sub>D</sub>		See <a href="#">Thermal Information</a>		
Operating junction temperature, T <sub>J</sub>		−40	150	°C
Storage temperature, T <sub>stg</sub>		−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground terminal.

### 7.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±750	
	Machine model (MM)	200	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Input voltage, V <sub>IN</sub>	2.7		6.5	V
Output voltage, V <sub>OUT</sub>	V <sub>IN</sub>		27	V
Inductor, L	4.7		10	μH
Input capacitor, C <sub>I</sub>	1			μF
Output capacitor, C <sub>O</sub>	1		2.2	μF
Compensation capacitor, C <sub>COMP</sub>		330		nF
PWM dimming signal frequency, f <sub>PWM</sub>	40		100	kHz
Operating ambient temperature, T <sub>A</sub>	−40		85	°C
Operating junction temperature, T <sub>J</sub>	−40		125	°C

### 7.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS61162D	UNIT
		YFF (DSBGA)	
		9 PINS	
θ <sub>JA</sub>	Junction-to-ambient thermal resistance	107	°C/W
θ <sub>JCtop</sub>	Junction-to-case (top) thermal resistance	0.9	°C/W
θ <sub>JB</sub>	Junction-to-board thermal resistance	18.1	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	4.0	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	18	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 7.5 Electrical Characteristics

$V_{IN} = 3.6\text{ V}$ , EN = high, PWM = high, IFB current = 20 mA, minimum and maximum values =  $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$ , typical values are at  $T_A = 25^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>POWER SUPPLY</b>						
$V_{IN}$	Input voltage range		2.7		6.5	V
$V_{VIN\_UVLO}$	Undervoltage lockout threshold	$V_{IN}$ falling		2.2	2.3	V
		$V_{IN}$ rising			2.45	
$V_{VIN\_HYS}$	VIN UVLO hysteresis			100		mV
$I_Q$	Operating quiescent current into VIN	Device enable, switching 1.2 MHz and no load, $V_{IN} = 3.6\text{ V}$		1.2	2	mA
$I_{SD}$	Shutdown current	EN = low		1	2	$\mu\text{A}$
<b>EN and PWM</b>						
$V_H$	EN logic high		1.2			V
$V_L$	EN logic Low				0.4	V
$V_H$	PWM logic high		1.2			V
$V_L$	PWM logic low				0.4	V
$R_{PD}$	EN pin and PWM pin internal pulldown resistor		400	800	1600	k $\Omega$
$t_{PWM\_SD}$	PWM logic low width to shutdown	PWM high to low	20			ms
$t_{EN\_SD}$	EN logic low width to shutdown	EN high to low	2.5			ms
<b>CURRENT REGULATION</b>						
$V_{ISET\_full}$	ISET pin voltage	Full brightness	1.204	1.229	1.253	V
$K_{ISET\_full}$	Current multiplier	Full brightness		1030		
$I_{FB\_avg}$	Current accuracy	$I_{ISET} = 20\ \mu\text{A}$ , D = 100%, $0^\circ\text{C}$ to $70^\circ\text{C}$	-2%		2%	
		$I_{ISET} = 20\ \mu\text{A}$ , D = 100%	-2.3%		2.3%	
$K_M$	$(I_{MAX} - I_{AVG}) / I_{AVG}$	D = 100%		1%	2%	
		D = 25%		1%		
$I_{IFB\_max}$	Current sink maximum output current	$I_{ISET} = 35\ \mu\text{A}$ , each IFBx pin	30			mA
<b>POWER SWITCH</b>						
$R_{DS(on)}$	Switch MOSFET on-resistance	$V_{IN} = 3.6\text{ V}$		0.25		$\Omega$
		$V_{IN} = 3\text{ V}$		0.3		
$I_{LEAK\_SW}$	Switch MOSFET leakage current	$V_{SW} = 35\text{ V}$ , $T_A = 25^\circ\text{C}$			1	$\mu\text{A}$
<b>OSCILLATOR</b>						
$f_{SW}$	Oscillator frequency		1000	1200	1500	kHz
$D_{max}$	Maximum duty cycle	Measured on the drive signal of switch MOSFET	91%	95%		
<b>BOOST VOLTAGE CONTROL</b>						
$V_{IFB\_reg}$	IFBx feedback regulation voltage	$I_{IFBx} = 20\text{ mA}$ , measured on IFBx pin which has a lower voltage		90		mV
$I_{sink}$	COMP pin sink current			12		$\mu\text{A}$
$I_{source}$	COMP pin source current			5		$\mu\text{A}$
$G_{ea}$	Error amplifier transconductance		30	55	80	$\mu\text{mho}$
$R_{ea}$	Error amplifier output resistance			45.5		M $\Omega$
$f_{ea}$	Error amplifier crossover frequency	5 pF connected to COMP pin		1.65		MHz

## Electrical Characteristics (continued)

$V_{IN} = 3.6\text{ V}$ , EN = high, PWM = high, IFB current = 20 mA, minimum and maximum values =  $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$ , typical values are at  $T_A = 25^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>PROTECTION</b>						
$I_{LIM}$	Switch MOSFET current limit	$D = D_{max}$ , $0^\circ\text{C}$ to $70^\circ\text{C}$	1	1.5	2	A
$I_{LIM\_Start}$	Switch MOSFET start-up current limit	$D = D_{max}$		0.7		A
$t_{Half\_LIM}$	Time window for half current limit			5		ms
$V_{OVP\_SW}$	SW pin overvoltage threshold		25	26.5	28	V
$V_{OVP\_IFB}$	IFBx pin overvoltage threshold	Measured on IFBx pin	4.2	4.5	4.8	V
$V_{ACKNL}$	Acknowledge output voltage low <sup>(1)</sup>	Open drain, $R_{pullup} = 15\text{ k}\Omega$ to $V_{IN}$			0.4	V
<b>THERMAL SHUTDOWN</b>						
$T_{shutdown}$	Thermal shutdown threshold			160		$^\circ\text{C}$
$T_{hys}$	Thermal shutdown hysteresis			15		$^\circ\text{C}$

- (1) Acknowledge condition active 0; this condition is only applied when the RFA bit is set to 1. To use this feature, master must have an open drain output, and the data line must be pulled up by the master with a resistor load.

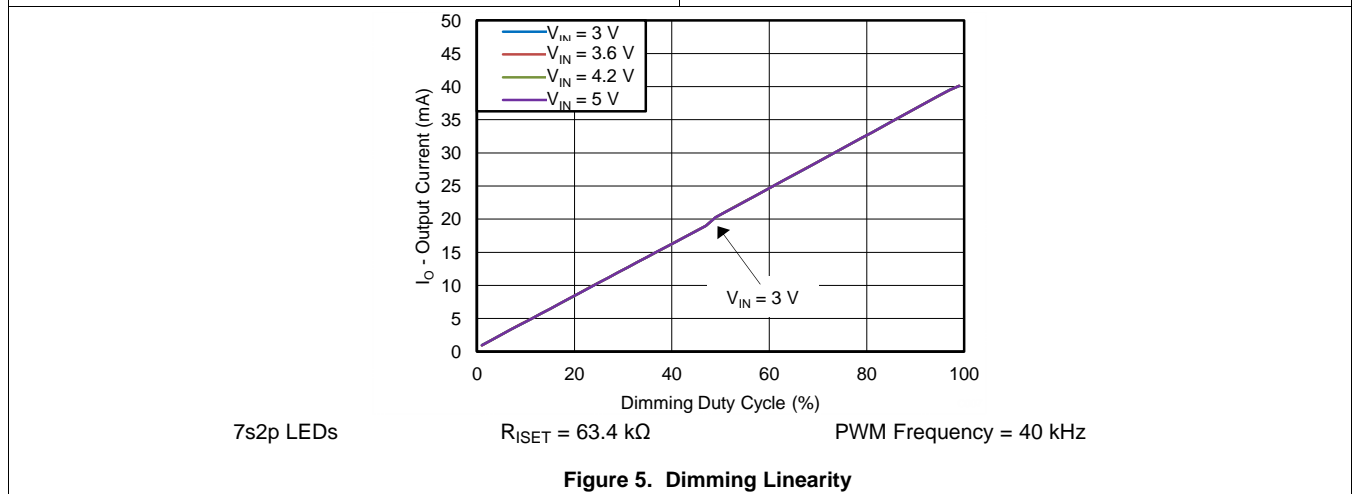
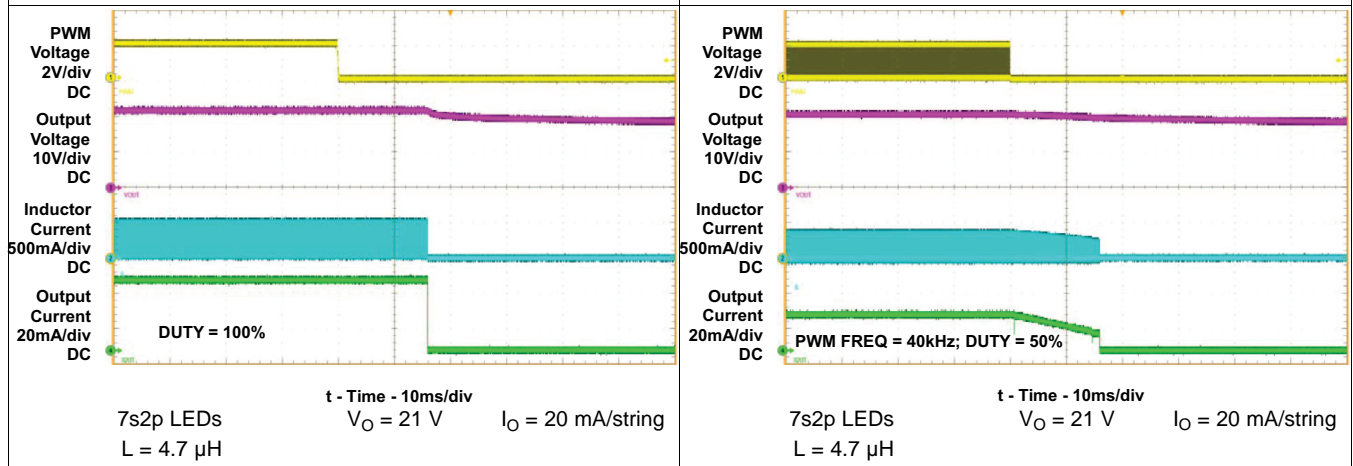
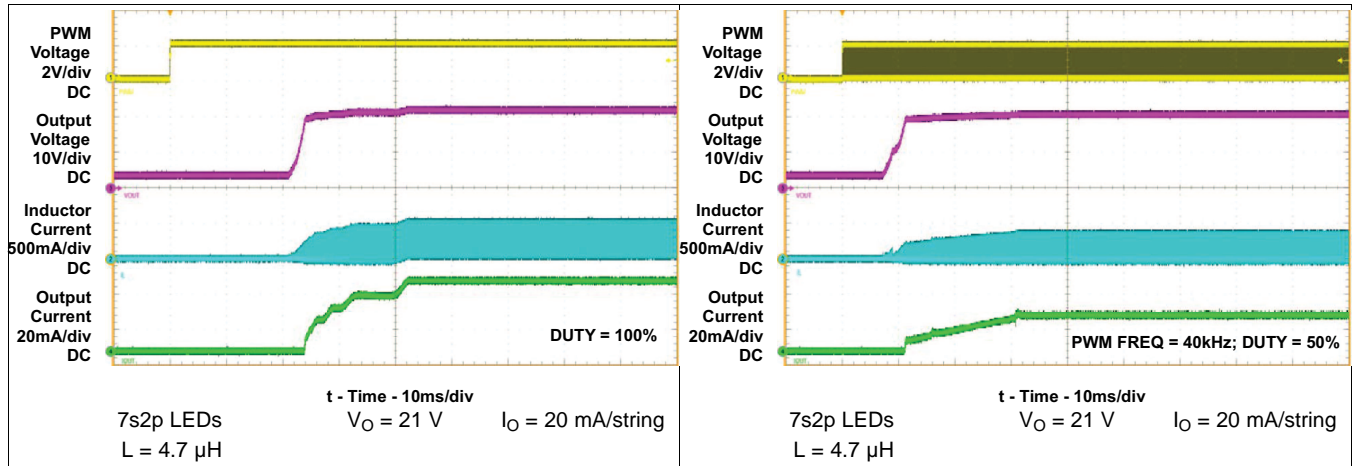
## 7.6 EasyScale Timing Requirements

		MIN	MAX	UNIT
$t_{es\_delay}$	EasyScale detection delay, measured from EN low to high	100		$\mu\text{s}$
$t_{es\_det}$	EasyScale detection time, EN pin low time	260		$\mu\text{s}$
$t_{es\_win}$	EasyScale detection window, easured from EN low to high <sup>(1)</sup>	1		ms
$t_{start}$	Start time of program stream	2		$\mu\text{s}$
$t_{EOS}$	End time of program stream	2	360	$\mu\text{s}$
$t_{H\_LB}$	High time of low bit (Logic 0)	2	180	$\mu\text{s}$
$t_{L\_LB}$	Low time of low bit (Logic 0)	$2 \times t_{H\_LB}$	360	$\mu\text{s}$
$t_{H\_HB}$	High time of high bit (Logic 1)	$2 \times t_{L\_HB}$	360	$\mu\text{s}$
$t_{L\_HB}$	Low time high bit (Logic 1)	2	180	$\mu\text{s}$
$t_{valACKN}$	Acknowledge valid time		2	$\mu\text{s}$
$t_{ACKN}$	Duration of acknowledge condition		512	$\mu\text{s}$

- (1) To select EasyScale interface, after  $t_{es\_delay}$  delay from EN low to high, drive EN pin to low for more than  $t_{es\_det}$  before  $t_{es\_win}$  expires.

## 7.7 Typical Characteristics

Ambient temperature is 25°C and  $V_{IN}$  is 3.6 V unless otherwise noted.



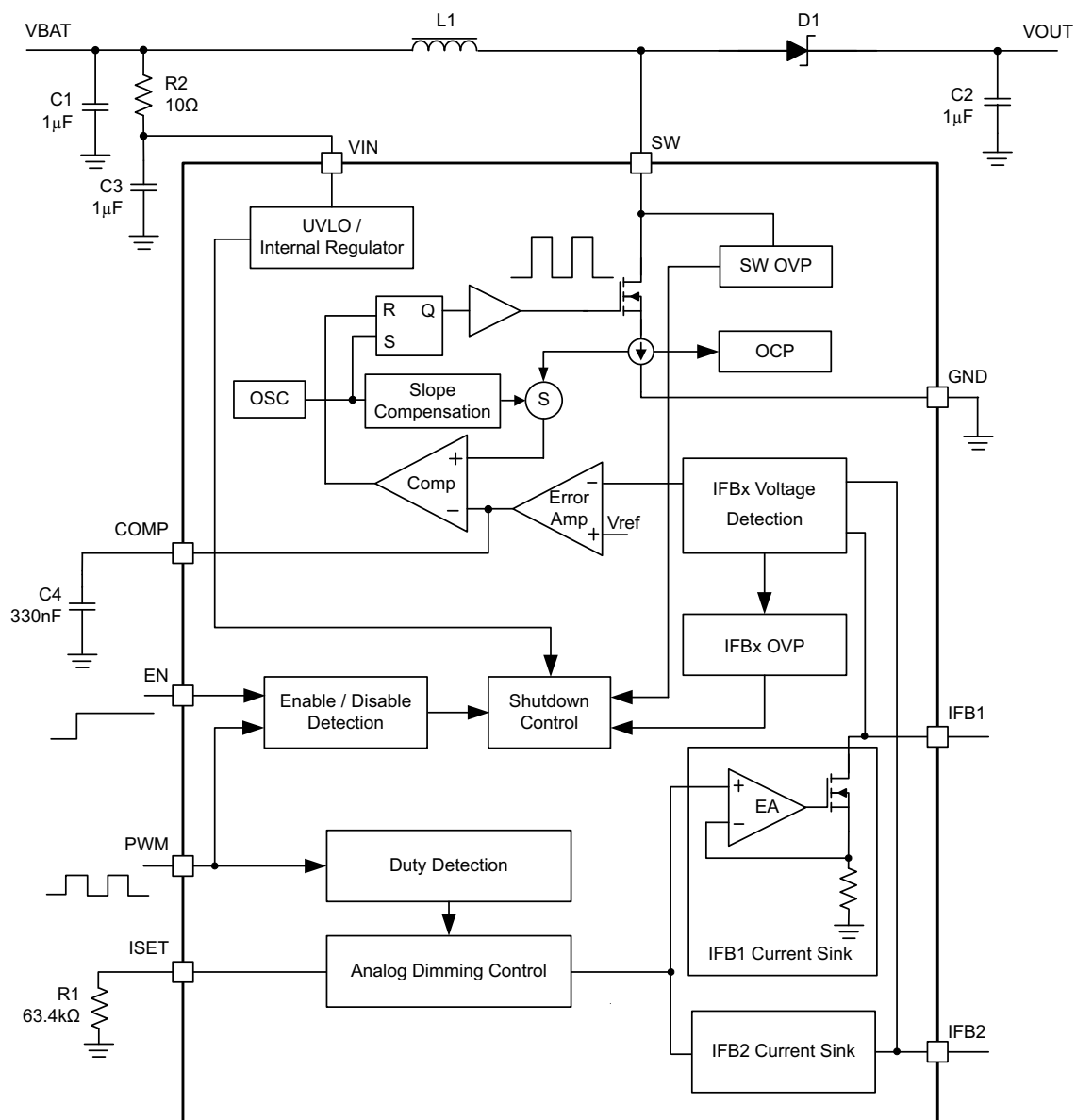
## 8 Detailed Description

### 8.1 Overview

The TPS61162D is a high-efficiency, dual-channel white LED driver for smart-phone backlighting applications. The device operates over the 2.7-V to 6.5-V input voltage range.

The TPS61162D consists of an inductive boost plus two current sink white-LED drivers designed to power one or two LED strings with up to ten LEDs each (up to 26.5 V typical), with a maximum of 30 mA per string. The power for the LED strings comes from an integrated asynchronous backlight boost converter operating at 1.2-MHz switching frequency. LED current is regulated by the low-headroom current sinks. The inductive backlight boost automatically adjusts its output voltage to keep the active current sinks in regulation, while minimizing current sink headroom voltage. Additionally, the TPS61162D includes protection circuits for overcurrent, overvoltage and thermal shutdown protection.

### 8.2 Functional Block Diagram





## 8.3 Feature Description

### 8.3.1 Normal Operation

In order to provide high brightness backlighting for large-sized or high-resolution smart-phone panels, a greater number of white LED diodes are used. Having all LED diodes in a string improves overall current matching; however, the output voltage of a boost converter is limited when input voltage is low, and normally the efficiency drops when the output voltage is very high. For these reasons, the TPS61162D is designed to configure the LED diodes in two parallel strings.

### 8.3.2 Boost Converter

The boost converter of the TPS61162D integrates a 40-V, 1.5-A low-side switch MOSFET and has a fixed switching frequency of 1.2 MHz. The control architecture is based on traditional current-mode PWM control. (For operation see [Functional Block Diagram](#).) Two current sinks regulate the dual-channel current, and the boost output is automatically set by the voltage of the regulating IFBx pin. The output of the error amplifier and the sensed current of the switch MOSFET are applied to a control comparator to generate the boost switching duty cycle; slope compensation is added to the current signal to allow stable operation for duty cycles larger than 50%.

In order to ensure that both current sinks remain in regulation whenever there is a mismatch in string voltages while the power dissipation of the current sink regulators is minimized, the minimum headroom voltage between IFB1 and IFB2 becomes the regulation point for the boost converter. For example, if the LEDs connected to IFB1 require 20 V, and the LEDs connected to IFB2 require 20.5 V at the programmed current, then the voltage at IFB2 is about 90 mV, and the voltage at IFB1 is about 0.59 V. In other words, the boost makes the cathode of the highest voltage LED string the regulation point.

### 8.3.3 IFBx Pin Unused

If only one channel is needed, a user can easily disable the unused channel by connecting its IFBx pin to ground. If both IFBx pins are connected to ground, the device does not start up.

### 8.3.4 Enable and Start-Up

In order to enable the device from shutdown mode, three conditions have to be met:

1. Power On Reset (POR), that is, VIN voltage is higher than UVLO threshold
2. Logic high on EN pin
3. PWM signal (logic high or PWM pulses) on PWM pin

When all these conditions are met, an internal LDO linear regulator is enabled to provide supply to internal circuits, and the device can start up.

The TPS61162D supports two dimming interfaces: one-wire digital interface (EasyScale interface) and PWM interface. The device begins an EasyScale detection window after start-up to detect which interface is selected. If the EasyScale interface is needed, signals of a specific pattern must be input into the EN pin during the EasyScale detection window; otherwise, PWM dimming interface is enabled (see details in [One-Wire Digital Interface \(Easyscale Interface\)](#)).

After the EasyScale detection window, the TPS61162D checks the status of IFBx pins. If one IFBx pin is detected to connect to ground, the corresponding channel is disabled and removed from the control loop. The soft start then begins, and the boost converter starts switching. If both IFBx pins are shorted to ground, the TPS61162D does not start up.

Either pulling EN pin low for more than 2.5 ms, or pulling the PWM pin low for more than 20 ms, can disable the device, and the TPS61162D enters into shutdown mode.

### 8.3.5 Soft Start

Soft start is implemented internally to prevent voltage overshoot and inrush current. After the IFBx pin status detection, the COMP pin voltage starts ramp up, and the boost starts switching. During the beginning 5 ms ( $t_{\text{Half\_LIM}}$ ) of the switching, the peak current of the switch MOSFET is limited at  $I_{\text{LIM\_Start}}$  (0.7 A typical) to prevent excess inrush input current. After 5 ms the current limit is changed to  $I_{\text{LIM}}$  (1.5 A typical) to allow the normal operation of the boost converter.

## Feature Description (continued)

### 8.3.6 Full-Scale Current Program

The dual channels of the TPS61162D can provide up to 30 mA current each — when either the EasyScale interface or PWM interface is selected, the full-scale current (current when dimming duty cycle is 100%) of each channel must be programmed by an external resistor  $R_{ISET}$  at ISET pin according to [Equation 1](#).

$$I_{FB\_full} = \frac{V_{ISET\_full}}{R_{ISET}} \times K_{ISET\_full}$$

where

- $I_{FB\_full}$  = full-scale current of each channel
- $K_{ISET\_full}$  = 1030 (Current multiple when dimming duty cycle = 100%)
- $V_{ISET\_full}$  = 1.229 V (ISET pin voltage when dimming duty cycle = 100%)
- $R_{ISET}$  = ISET pin resistor

(1)

### 8.3.7 Brightness Control

The TPS61162D controls the DC current of the dual channels to realize the brightness dimming. The DC current control is normally referred to as analog dimming mode. When the DC current of LED diode is reduced, the brightness is dimmed.

The TPS61162D can receive either the PWM signals at the PWM pin (PWM interface) or digital commands at the EN pin (EasyScale interface) for brightness dimming. If the EasyScale interface is selected, the PWM pin must be kept high; if PWM interface is selected, the EN pin must be kept high.

### 8.3.8 Undervoltage Lockout

An undervoltage lockout circuit prevents the operation of the device at input voltages below undervoltage threshold (2.2 V typical). When the input voltage is below the threshold, the device is shut down. If the input voltage rises by undervoltage lockout hysteresis, the device restarts.

### 8.3.9 Overvoltage Protection

Overvoltage protection circuitry prevents device damage as the result of white LED string disconnection or shortage.

The TPS61162D monitors the voltages at the SW and IFBx pins during each switching cycle. If either SW OVP threshold  $V_{OVP\_SW}$  or IFBx OVP threshold  $V_{OVP\_FB}$  is reached due to the LED string open or short issue, the protection circuitry is triggered. Refer to [Figure 6](#) and [Figure 7](#) for the protection actions.

If one LED string is open, its IFBx pin voltage drops, and the boost output voltage is increased by the control loop as it tries to regulate this lower IFBx voltage to the target value (90 mV typical). The current of the normally operating string is properly regulated but its IFBx voltage rises because of the rise in output voltage. During this process, either the SW voltage reaches the OVP threshold  $V_{OVP\_SW}$  or the IFBx voltage of the normally operating string reaches its overvoltage threshold  $V_{OVP\_FB}$ , and the corresponding protection mechanism is triggered.

If both LED strings are open, the voltages of both IFBx pins drop to ground, and the boost output voltage is increased by the control loop until it reaches the SW OVP threshold  $V_{OVP\_SW}$ . At that point the SW OVP protection circuitry is triggered, and the device is latched off. Only the VIN POR pin or EN/PWM pin toggling can restart the device.

One LED diode short in a string is allowed in the TPS61162D. If one LED diode in a string is short, the IFBx voltage of the normal string is regulated to about 90 mV, and the IFBx pin voltage of the abnormal string is higher. Typically with only one diode short, the higher IFBx pin voltage does not reach the IFBx OVP threshold  $V_{OVP\_FB}$ , so the protection circuitry is not triggered.

If more than one LED diodes are short in a string, as the boost loop regulates the IFBx normal string voltage to 90 mV, the IFBx pin voltage of the abnormal string is much higher and reaches  $V_{OVP\_FB}$  — then the protection circuitry is triggered.

SW OVP protection is also triggered when the forward voltage drop of an LED string exceeds the SW OVP threshold. In this case, the device turns off the switch FET and shuts down.

Feature Description (continued)

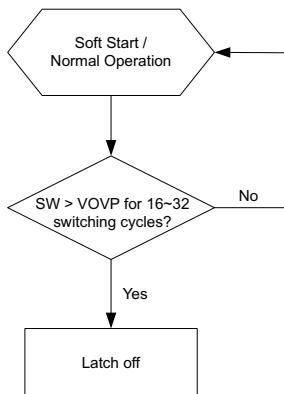


Figure 6. SW OVP Protection Action

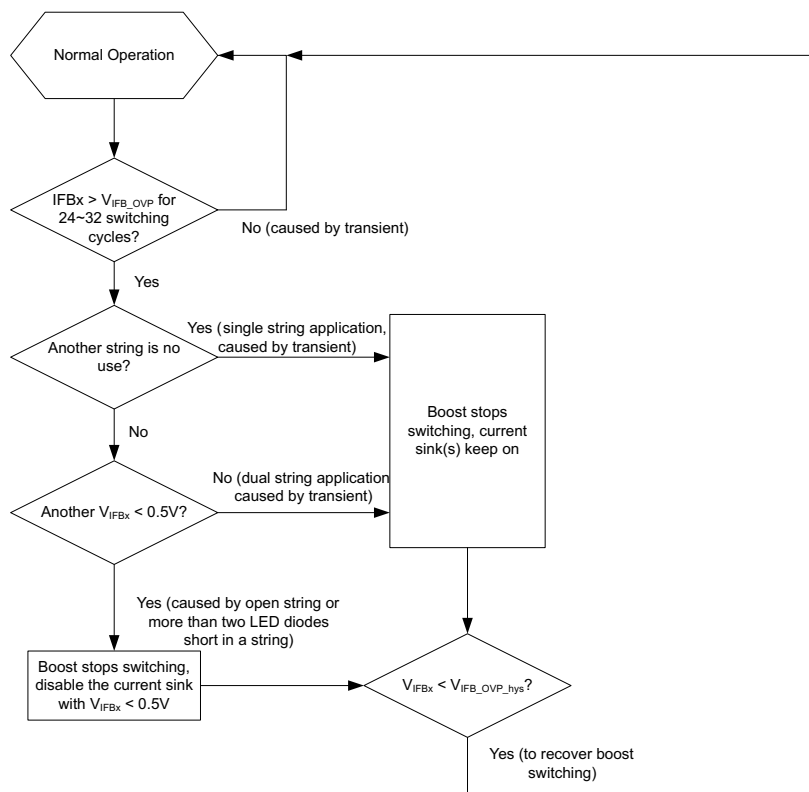


Figure 7. VIFBx OVP Protection Action

8.3.10 Overcurrent Protection

The TPS61162D has a pulse-by-pulse overcurrent limit. The boost switch turns off when the inductor current reaches this current threshold, and it remains off until the beginning of the next switching cycle. This protects the TPS61162D and external components under overload conditions.

8.3.11 Thermal Shutdown

An internal thermal shutdown turns off the device when the typical junction temperature of 160°C is exceeded. The device is released from shutdown automatically when the junction temperature decreases by 15°C.

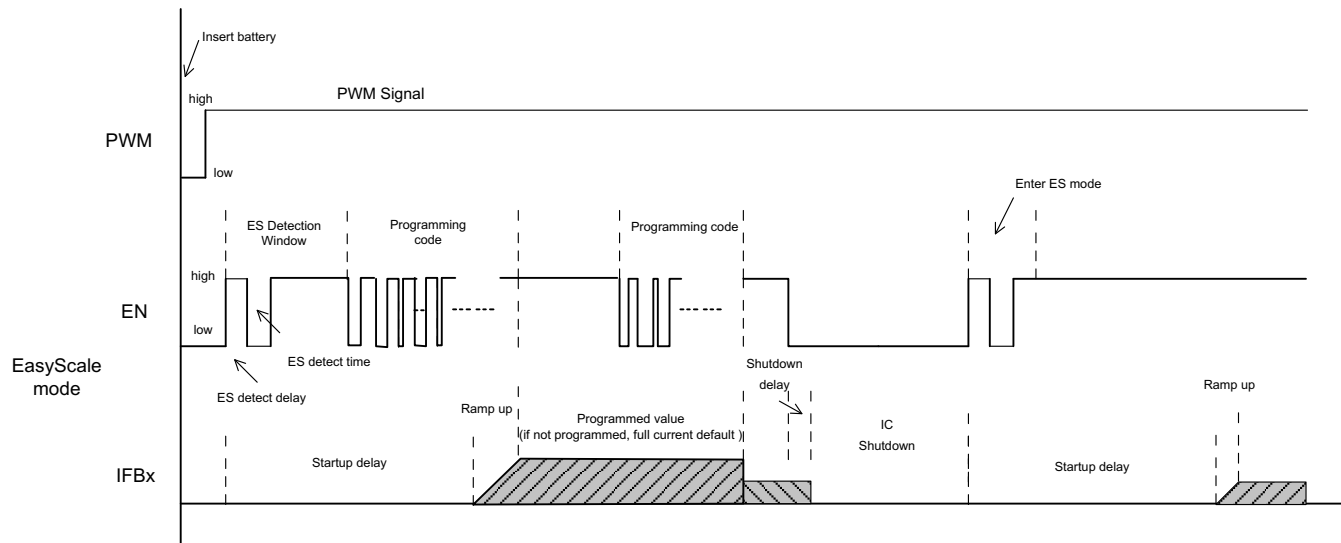
## 8.4 Device Functional Modes

### 8.4.1 One-Wire Digital Interface (Easyscale Interface)

The EN pin features a simple digital interface to allow digital brightness control. The digital dimming interface can save the processor power and battery life as it does not require PWM signals all the time, and the processor can enter idle mode if possible. In order to enable the EasyScale interface, the following conditions must be satisfied, and the specific digital pattern on the EN pin must be recognized by the device every time the TPS61162D starts up from shutdown mode:

1. VIN voltage is higher than UVLO threshold and PWM pin is pulled high.
2. Pull the EN pin from low to high to enable the TPS61162D. At this moment, the EasyScale detection window starts.
3. After EasyScale detection delay time ( $t_{es\_delay} = 100 \mu s$ ), drive EN to low for greater than EasyScale detection time ( $t_{es\_detect} = 260 \mu s$ ).

The third step must be finished before the EasyScale detection window ( $t_{es\_win} = 1 ms$ ) expires; once this step is finished, the EasyScale interface is enabled, and the EasyScale communication can start. Refer to the [Figure 8](#) for a graphical explanation.



**Figure 8. EasyScale Interface Detection**

The TPS61162D supports 9-bit brightness code programming. Using the EasyScale interface, a master can program the 9-bit code D8(MSB) to D0(LSB) to any of 511 steps with a single command. The default code value of D8 to D0 is 11111111 when the device is first enabled, and the programmed value is stored in an internal register and set the dual-channel current according to [Equation 2](#). The code is reset to default value when the device is shut down or disabled.

$$I_{FBx} = I_{FB\_full} \times \frac{Code}{511}$$

where

- $I_{FB\_full}$  = the full-scale LED current set by the  $R_{ISET}$  at ISET pin
- Code = the 9-bit brightness code D8 - D0 programmed by the EasyScale interface (2)

When the one-wire digital interface at EN pin is selected, the PWM pin can be connected to either the VIN pin or a GPIO (refer to [Additional Application Circuits](#)). If the PWM pin is connected to the VIN pin, the EN pin alone can enable and disable the device:

- Pulling the EN pin low for more than 2.5 ms disables the device.
- If the PWM pin is connected to a GPIO, both PWM and EN signals must be high to enable the device.
- Either pulling EN pin low for more than 2.5 ms or pulling PWM pin low for more than 20 ms disables the device.

## Device Functional Modes (continued)

### 8.4.2 PWM Control Interface

The PWM control interface is automatically enabled if the EasyScale interface fails to be enabled during start-up. In this case, the TPS61162D receives PWM dimming signals on the PWM pin to control the backlight brightness. When using PWM interface, the EN pin can be connected to the VIN pin or a GPIO (refer to [Additional Application Circuits](#)). If the EN pin is connected to the VIN pin, the PWM pin alone is used to enable and disable the device; applying a signal at the PWM pin enables the device; pulling the PWM pin low for more than 20 ms disables the device; if the EN pin is connected to a GPIO, either pulling the EN pin low for more than 2.5 ms or pulling the PWM pin low for more than 20 ms disables the device. Only after both EN and PWM signals are applied can the TPS61162D start up (see [Figure 9](#)).

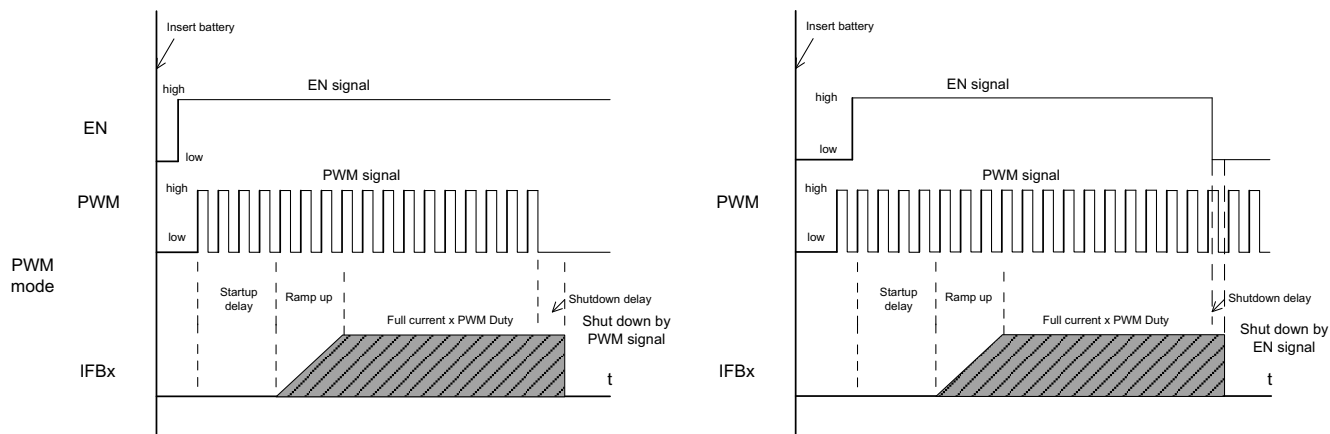


Figure 9. PWM Control Interface Detection

When the PWM pin is constantly high, the dual channel current is regulated to full scale according to [Equation 1](#). The PWM pin allows PWM signals to reduce this regulation current according to the PWM duty cycle; therefore, it achieves LED brightness dimming. The relationship between the PWM duty cycle and the IFBx current is given by [Equation 3](#).

$$I_{FBx} = I_{FB\_full} \times \text{Duty}$$

where

- $I_{FBx}$  = the current of each current sink
  - $I_{FB\_full}$  = the full-scale LED current
  - Duty = the duty cycle information detected from the PWM signals
- (3)

## 8.5 Programming

### 8.5.1 EasyScale Programming

EasyScale is a simple and flexible one-pin interface used to configure the current of the dual channels. The interface is based on a master-slave structure, where the master is typically a microcontroller or application processor and the device is the slave. [Figure 10](#) and [Table 1](#) give an overview of the protocol used by TPS61162D. A command consists of 24 bits, including an 8-bit device address byte and a 16-bit data byte. All 24 bits must be transmitted together each time, and the LSB bit must be transmitted first. The device address byte D7(MSB) to D0(LSB) is fixed to 0x8F. The data byte includes 9 bits D8(MSB) to D0(LSB) for brightness information and an RFA bit. The RFA bit set to 1 indicates the Request for Acknowledge condition. The Acknowledge condition is only applied when the protocol is received correctly. The advantage of EasyScale compared with other one-pin interfaces is that its bit detection is, to a large extent, independent from the bit transmission rate. EasyScale can automatically detect bit rates from 1.7 kBit/second up to 160 kBit/second.

Programming (continued)

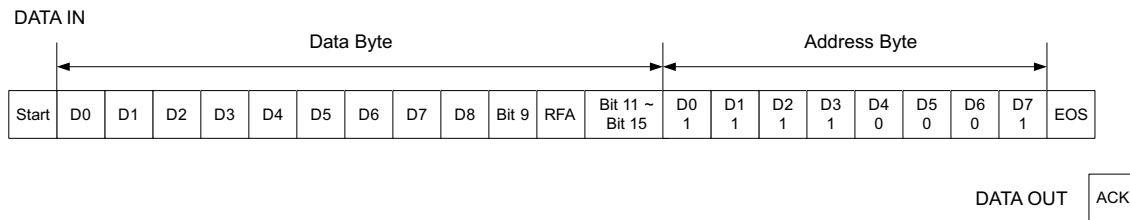


Figure 10. EasyScale Protocol Overview

Table 1. EasyScale Bit Description

BYTE	BIT NUMBER	NAME	TRANSMISSION DIRECTION	DESCRIPTION
Device Address Byte (0x8F)	23 (MSB)	DA7	IN	DA7 = 1, MSB of device address
	22	DA6		DA6 = 0
	21	DA5		DA5 = 0
	20	DA4		DA4 = 0
	19	DA3		DA3 = 1
	18	DA2		DA2 = 1
	17	DA1		DA1 = 1
	16	DA0		DA0 = 1, LSB of device address
Data Byte	15	Bit 15	IN	No information. Write 0 to this bit.
	14	Bit 14		No information. Write 0 to this bit.
	13	Bit 13		No information. Write 0 to this bit.
	12	Bit 12		No information. Write 0 to this bit.
	11	Bit 11		No information. Write 0 to this bit.
	10	RFA		Request for acknowledge. If set to 1, the device pulls low the data line when it receives the command well. This feature can only be used when the master has an open drain output stage and the data line needs to be pulled high by the master with a pullup resistor; otherwise, acknowledge condition is not allowed and don't set this bit to 1.
	9	Bit 9		No information. Write 0 to this bit.
	8	D8		Data bit 8, MSB of brightness code
	7	D7		Data bit 7
	6	D6		Data bit 6
	5	D5		Data bit 5
	4	D4		Data bit 4
	3	D3		Data bit 3
	2	D2		Data bit 2
1	D1	Data bit 1		
0 (LSB)	D0	Data bit 0, LSB of brightness code		

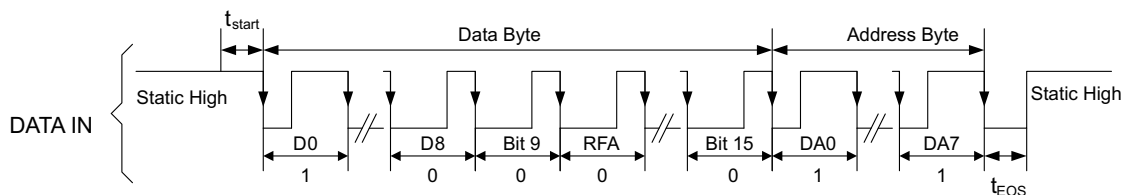


Figure 11. EasyScale Timing With RFA = 0

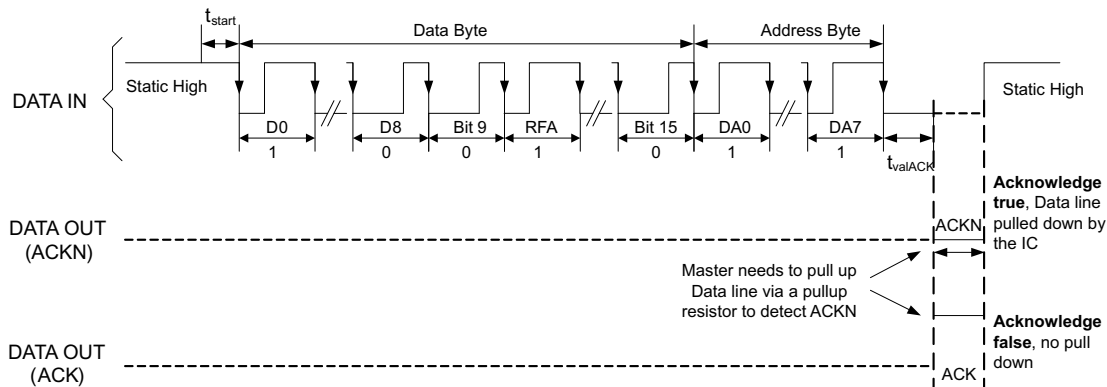


Figure 12. EasyScale Timing With RFA = 1

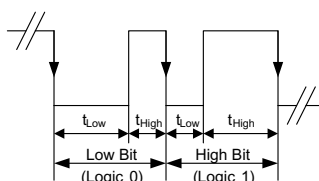


Figure 13. Easyscale — Bit Coding

The 24-bit command must be transmitted with LSB first and MSB last. Figure 11 shows the protocol without acknowledge request (Bit RFA = 0), Figure 12 with acknowledge request (Bit RFA = 1). Before the command transmission, a start condition must be applied. For this, the EN pin must be pulled high for at least  $t_{start}$  (2  $\mu$ s) before the bit transmission starts with the falling edge. If the EN pin is already at high level, no start condition is needed. The transmission of each command is closed with an End of Stream condition for at least  $t_{EOS}$  (2  $\mu$ s).

The bit detection is based on a Logic Detection scheme, where the criterion is the relation between  $t_{LOW}$  and  $t_{HIGH}$  (refer to Figure 13). It can be simplified to:

Low Bit (Logic 0):  $t_{LOW} \geq 2 \times t_{HIGH}$

High Bit (Logic 1):  $t_{HIGH} \geq 2 \times t_{LOW}$

The bit detection starts with a falling edge on the EN pin and ends with the next falling edge. Depending on the relation between  $t_{HIGH}$  and  $t_{LOW}$ , the logic 0 or 1 is detected.

The acknowledge condition is only applied if:

- Acknowledge is requested by setting RFA bit to 1.
- The transmitted device address matches with the device address of the device.
- A total of 24 bits are received correctly.

If above conditions are met, after  $t_{valACK}$  delay from the moment when the last falling edge of the protocol is detected, an internal ACKN-MOSFET is turned on to pull the EN pin low for the time  $t_{ACKN}$ , which is 512  $\mu$ s maximum, then the acknowledge condition is valid. During the  $t_{valACK}$  delay, the master controller keeps the line low; after the delay, it must release the line by outputting high impedance and then detect the acknowledge condition. If it reads back a logic 0, the device has received the command correctly. The EN pin can be used again by the master when the acknowledge condition ends after  $t_{ACKN}$  time.

Note that the acknowledge condition can only be requested when the master device has an open drain output. For a push-pull output stage, the use of a series resistor in the EN line to limit the current to 500  $\mu$ A is recommended to for such cases as:

- An accidentally requested acknowledge, or
- To protect the internal ACKN-MOSFET.

## 9 Application and Implementation

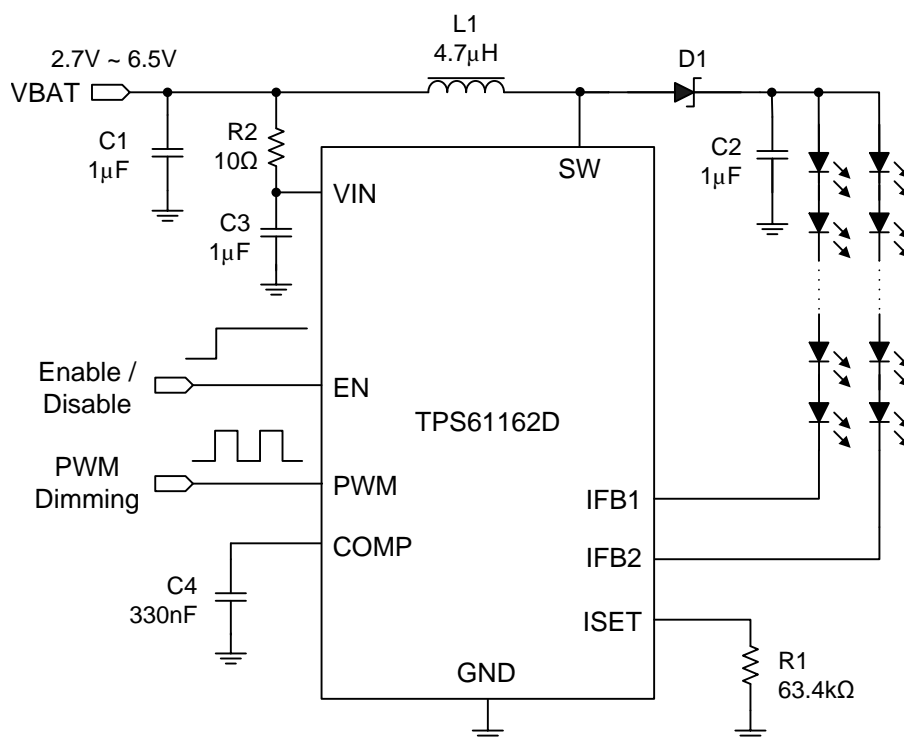
### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The TPS61162D provides a complete high-performance LED lighting solution for mobile handsets. It can drive up to 2 strings of white LEDs with up to 10 LEDs per string. A boost converter generates the high voltage required for the LEDs. LED brightness can be controlled either by the PWM dimming interface or by the single-wire EasyScale dimming interface.

### 9.2 Typical Application



**Figure 14. TPS61162D Typical Application**

#### 9.2.1 Design Requirements

For typical WLED-driver applications, use the parameters listed in [Table 2](#).

**Table 2. Design Parameters**

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	2.7 V to 6.5 V
Boost switching frequency (maximum)	1500 kHz
Efficiency	up to 90%



## 9.2.2 Detailed Design Procedure

### 9.2.2.1 Inductor Selection

Because the selection of inductor affects steady-state operation of the power supply, transient behavior, loop stability, and boost converter efficiency, the inductor is one of the most important components in switching power regulator design. There are three specifications most important to performance of the inductor: inductor value, DC resistance (DCR), and saturation current. The TPS61162D is designed to work with inductor values from 4.7  $\mu\text{H}$  to 10  $\mu\text{H}$  to support all applications. A 4.7- $\mu\text{H}$  inductor is typically available in a smaller or lower profile package, while a 10- $\mu\text{H}$  inductor produces lower inductor ripple. If the boost output current is limited by the overcurrent protection of the device, using a 10- $\mu\text{H}$  inductor may maximize the output current capability of the controller. A 22- $\mu\text{H}$  inductor can also be used for some applications, such as 6s2p and 7s2p, but may cause stability issues when more than eight WLED diodes are connected per string. Therefore, customers must verify the inductor in their application if it is different from the values in [Recommended Operating Conditions](#).

Inductor values can have  $\pm 20\%$  or even  $\pm 30\%$  tolerance with no current bias. When the inductor current approaches saturation level, its inductance can decrease 20% to 35% from the 0-A value depending on how the inductor vendor defines saturation. When selecting an inductor, user must confirm its rated current, especially the saturation current, is larger than its peak current during the operation.

Follow [Equation 4](#) to [Equation 6](#) to calculate the peak current of the inductor. To calculate the worst-case current, use the minimum input voltage, maximum output voltage, and maximum load current of the application. In order to leave enough design margin, the minimum switching frequency (1 MHz for TPS61162D), the inductor value with  $-30\%$  tolerance, and a low power conversion efficiency, such as 80% or lower are recommended for the calculation.

In a boost regulator, the inductor DC current can be calculated as [Equation 4](#).

$$I_{\text{DC}} = \frac{V_{\text{OUT}} \times I_{\text{OUT}}}{V_{\text{IN}} \times \eta}$$

where

- $V_{\text{OUT}}$  = boost output voltage
  - $I_{\text{OUT}}$  = boost output current
  - $V_{\text{IN}}$  = boost input voltage
  - $\eta$  = boost power conversion efficiency
- (4)

The inductor current peak-to-peak ripple can be calculated as [Equation 5](#).

$$I_{\text{PP}} = \frac{1}{L \times \left( \frac{1}{V_{\text{OUT}} - V_{\text{IN}}} + \frac{1}{V_{\text{IN}}} \right) \times F_{\text{S}}}$$

where

- $I_{\text{PP}}$  = inductor peak-to-peak ripple
  - $L$  = inductor value
  - $F_{\text{S}}$  = boost switching frequency
  - $V_{\text{OUT}}$  = boost output voltage
  - $V_{\text{IN}}$  = boost input voltage
- (5)

Therefore, the peak current  $I_{\text{P}}$  detected by the inductor is calculated with [Equation 6](#).

$$I_{\text{P}} = I_{\text{DC}} + \frac{I_{\text{PP}}}{2}$$
(6)

Select an inductor with saturation current over the calculated peak current. If the calculated peak current is larger than the switch MOSFET current limit  $I_{\text{LIM}}$ , use a larger inductor, such as 10  $\mu\text{H}$ , and make sure its peak current is below  $I_{\text{LIM}}$ .

Boost converter efficiency is dependent on the resistance of its current path, the switching losses associated with the switch MOSFET and power diode, and core loss of the inductor. The TPS61162D has optimized the internal switch resistance, however, the overall efficiency is affected a lot by the DCR of the inductor, equivalent series resistance (ESR) at the switching frequency, and the core loss. Core loss is related to the core material, and different inductors have different core loss. For a certain inductor, larger current ripple generates higher DCR/ESR conduction losses as well as higher core loss. Inductor data sheets do not typically provide the ESR and core loss information; if needed, consult the inductor vendor for detailed information. Generally, TI recommends an inductor with lower DCR/ESR for the TPS61162D application. However, there is a trade-off between the inductance of the inductor, DCR/ESR resistance, and the inductor footprint; furthermore, shielded inductors typically have higher DCR than unshielded ones. [Table 3](#) lists some recommended inductors for the TPS61162D. Verify whether the recommended inductor can support the target application using [Equation 4](#), [Equation 5](#), and [Equation 6](#) as well as bench validation.

**Table 3. Recommended Inductors**

PART NUMBER	L (μH)	DCR MAX (mΩ)	SATURATION CURRENT (A)	SIZE (L × W × H mm)	VENDOR
LPS4018-472ML	4.7	125	1.9	4 × 4 × 1.8	Coilcraft
LPS4018-682ML	6.8	150	1.3	4 × 4 × 1.8	Coilcraft
LPS4018-103ML	10	200	1.3	4 × 4 × 1.8	Coilcraft
PCMB051B-4R7M	4.7	163	2.7	5.4 × 5.2 × 1.2	Cyntec
PCMB051B-6R8M	6.8	250	2.3	5.4 × 5.2 × 1.2	Cyntec

### 9.2.2.2 Schottky Diode Selection

The TPS61162D demands a low forward voltage, high-speed, and low-capacitance Schottky diode for optimum efficiency. Ensure that the diode average and peak current rating exceeds the average output current and peak inductor current. In addition, the reverse breakdown voltage of the diode must exceed the open LED-protection voltage. TI recommends ONSem MBR0540 and NSR05F40 and Vishay MSS1P4 for the TPS61162D.

### 9.2.2.3 Compensation Capacitor Selection

The compensation capacitor C4 (refer to [Additional Application Circuits](#)) connected from the COMP pin to GND, is used to stabilize the feedback loop of the TPS61162D. A 330-nF ceramic capacitor for C4 is suitable for most applications. A 470-nF is also acceptable for some applications, and customers are suggested to verify it in their applications.

### 9.2.2.4 Output Capacitor Selection

Selection of the output capacitor is primarily to meet the requirement for the output ripple and loop stability. The output ripple voltage is related to the capacitance and the ESR of the capacitor. A 1-μF to 2.2-μF ceramic type X5R or X7R capacitor is recommended. Ceramic capacitors have low ESR so the contribution of the ESR component to the output ripple is negligible. Assuming a capacitor with zero ESR, the output ripple can be calculated with [Equation 7](#).

$$V_{\text{ripple}} = \frac{(V_{\text{OUT}} - V_{\text{IN}}) \times I_{\text{OUT}}}{V_{\text{OUT}} \times F_{\text{S}} \times C_{\text{OUT}}}$$

where

- $V_{\text{ripple}}$  = peak-to-peak output ripple (7)

The additional part of ripple caused by the ESR is calculated using  $V_{\text{ripple\_ESR}} = I_{\text{OUT}} \times R_{\text{ESR}}$  and can be ignored for ceramic capacitors.

#### NOTE

Capacitor degradation greatly increases the ripple. Select a capacitor with 50-V rated voltage to reduce the degradation at the output voltage. If the output ripple is too large, choosing a capacitor with less of a degradation effect or with a higher-rated voltage could be helpful.

### 9.2.3 Application Curves

Ambient temperature is 25°C and  $V_{IN}$  is 3.6 V, unless otherwise noted.

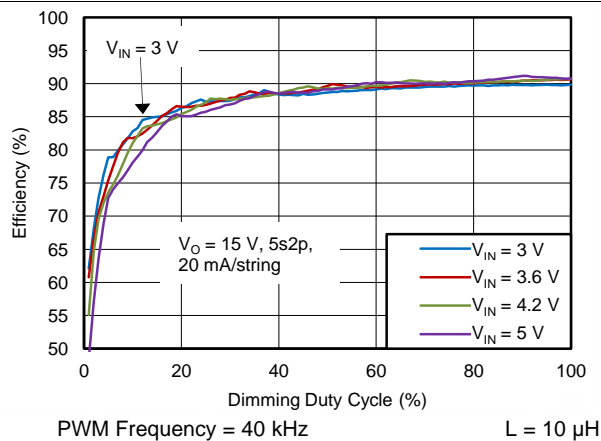


Figure 15. Efficiency vs Dimming Duty Cycle

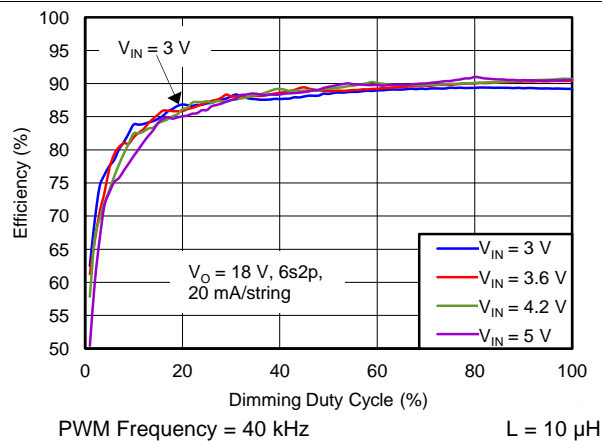


Figure 16. Efficiency vs Dimming Duty Cycle

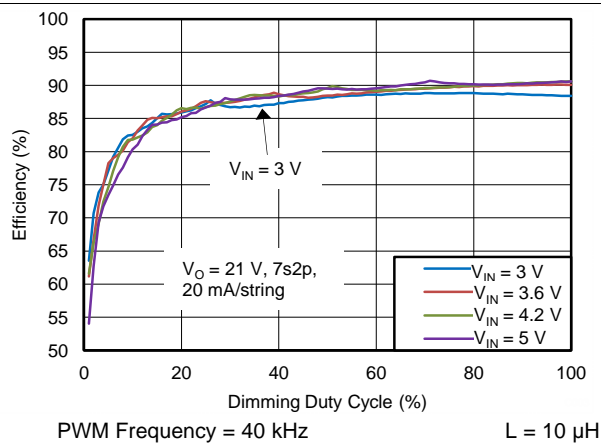


Figure 17. Efficiency vs Dimming Duty Cycle

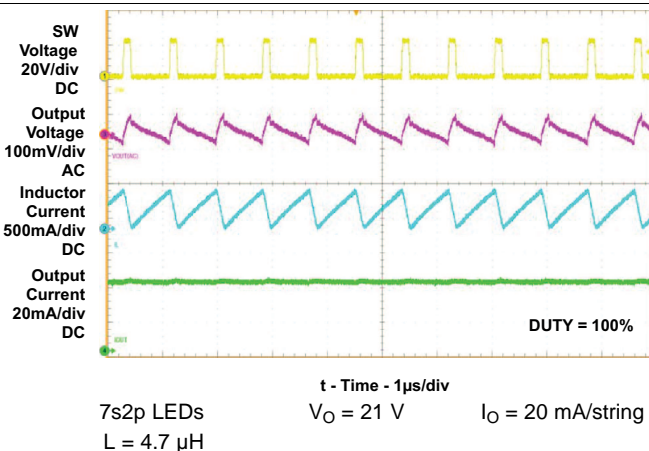


Figure 18. Switching Waveform

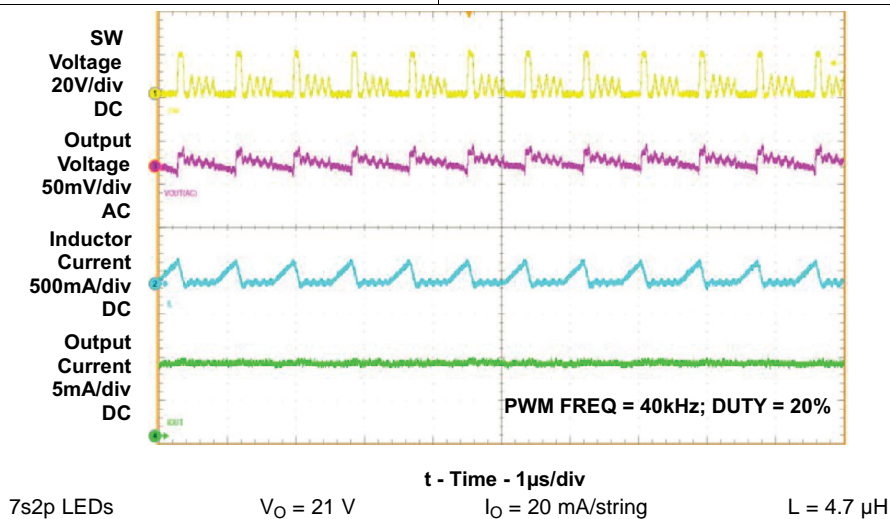
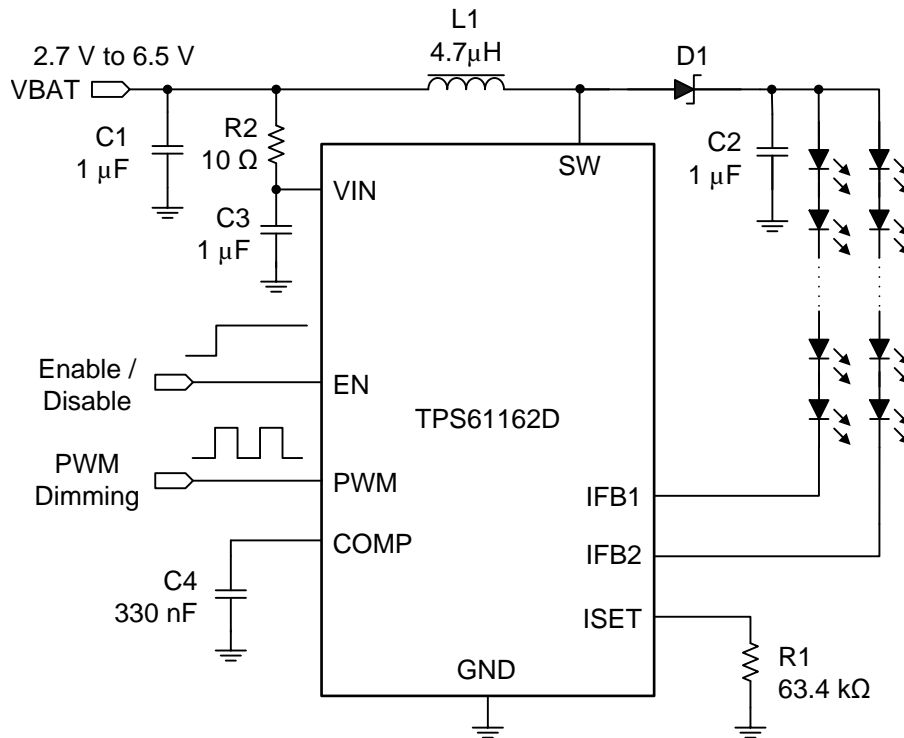
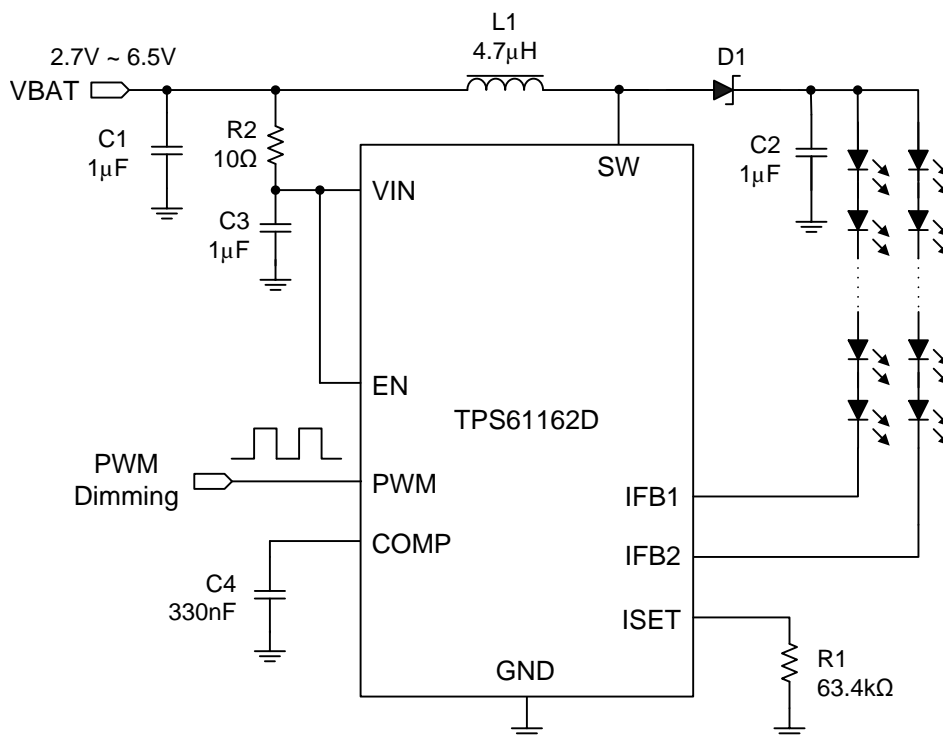


Figure 19. Switching Waveform

**9.2.4 Additional Application Circuits**


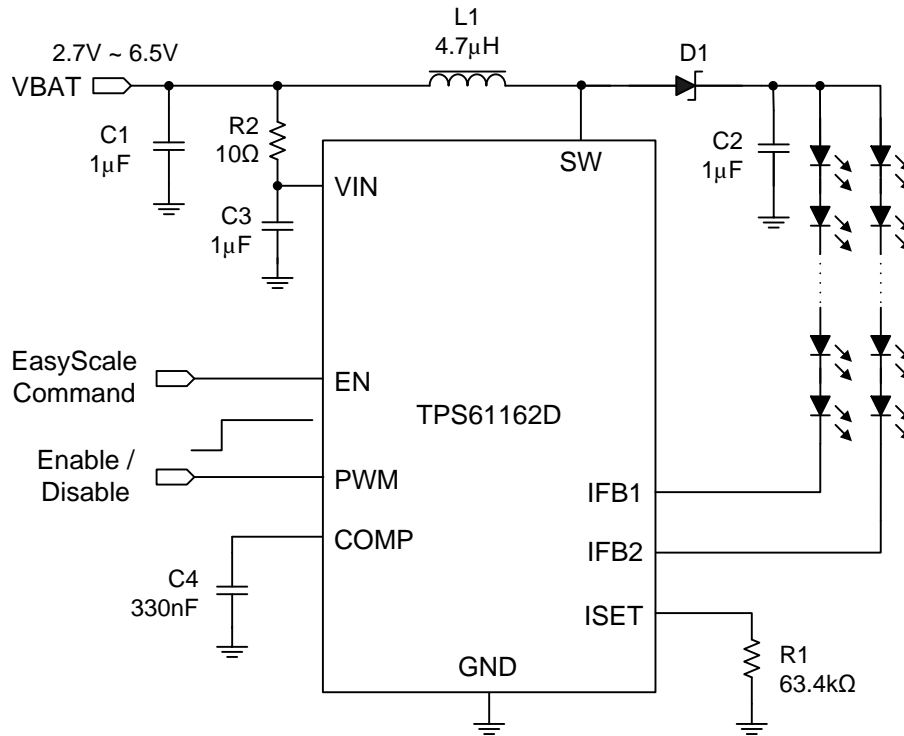
The EN pin can be used to enable or disable the device.

**Figure 20. TPS61162D Typical Application - PWM Interface Enabled**



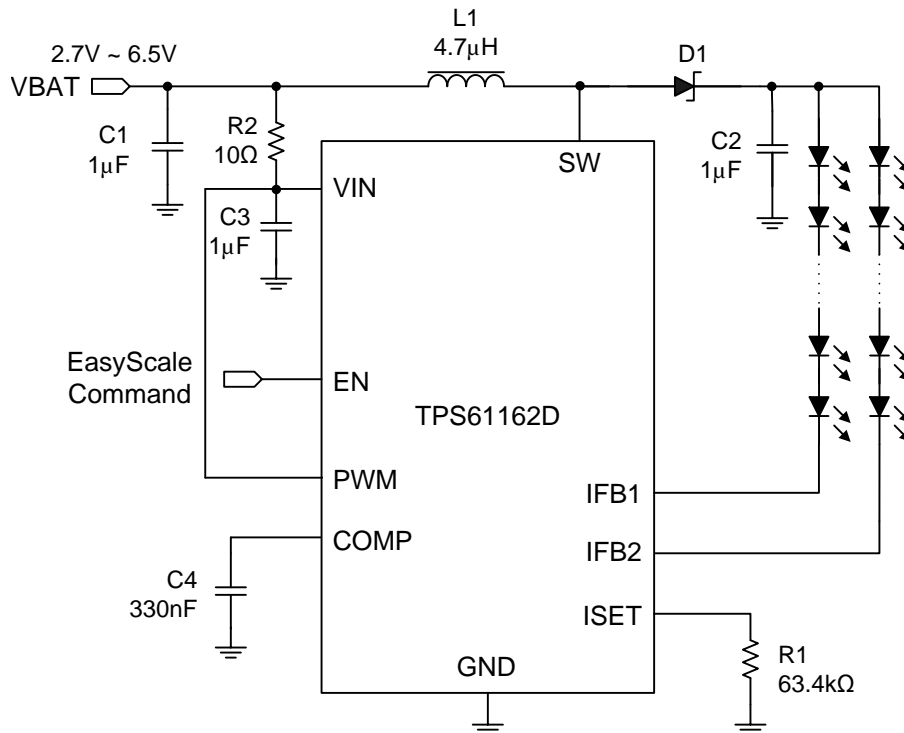
The EN pin is connected to  $V_{IN}$ ; only the PWM signal is used to enable or disable the device.

**Figure 21. TPS61162D Typical Application - PWM Interface Enabled**



The PWM pin can be used to enable or disable the device.

**Figure 22. TPS61162D Typical Application - One-Wire Digital Interface Enabled**



The PWM pin is connected to  $V_{IN}$ ; only the EN signal is used to enable or disable the device.

**Figure 23. TPS61162D Typical Application (One-Wire Digital Interface Enabled - )**

## 10 Power Supply Recommendations

The TPS61162D is designed to operate from an input supply range of 2.7 V to 6.5 V. This input supply should be well regulated and be able to provide the peak current required by the LED configuration and inductor selected without voltage drop under load transients (start-up or rapid brightness change). If the input supply is located far from the device, additional bulk capacitance may be required in addition to the ceramic bypass capacitors.

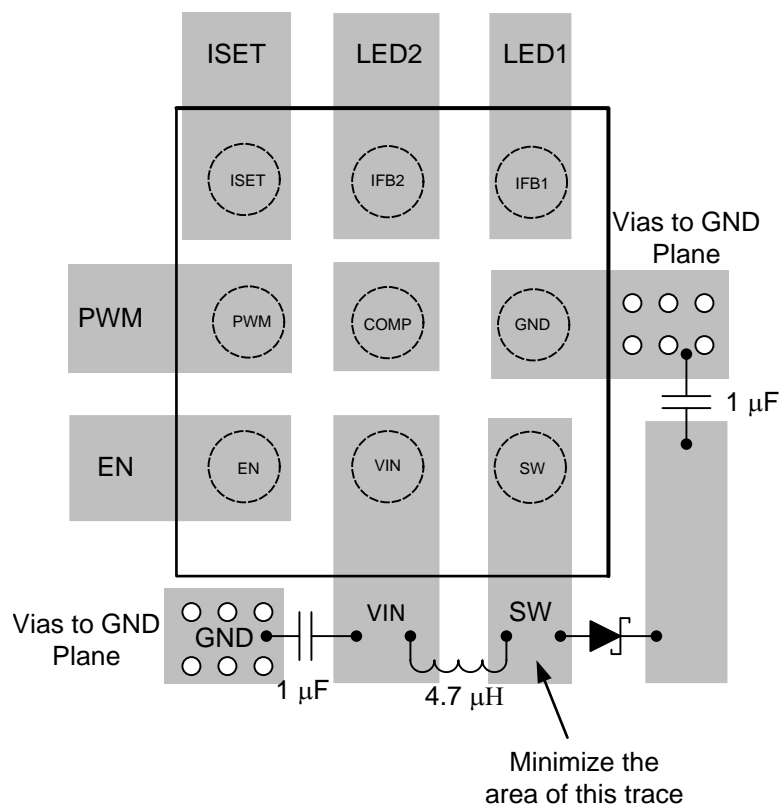
## 11 Layout

### 11.1 Layout Guidelines

As for all switching power supplies, especially those providing high current and using high switching frequencies, layout is an important design step. If layout is not carefully done, the regulator could show instability as well as EMI problems. Therefore, use wide and short traces for high current paths. The input capacitor, C1 in the Figure 14, must be close to the inductor, as well as the VIN and GND pins, in order to reduce the input ripple detected by the device. If possible, choose a higher capacitance value for C1. If the ripple seen at VIN pin is so great that it affects the boost loop stability or internal circuits operation, TI recommends R2 and C3 to filter and decouple the noise. In this case, C3 must be placed as close to the VIN and GND pins as possible.

The SW pin carries high current with fast rising and falling edges. Therefore, the connection between the SW pin to the inductor and Schottky diode must be kept as short and wide as possible. The trace between the Schottky diode and the output capacitor C2 must also be as short and wide as possible. It is beneficial to have the ground of the output capacitor C2 close to the GND pin because there is a large ground return current flowing between them. When laying out signal grounds, TI recommends using short traces separated from power ground traces, and connecting them together at a single point close to the GND pin.

### 11.2 Layout Example



**Figure 24. TPS61162D Layout Example**

## 12 Device and Documentation Support

### 12.1 Device Support

#### 12.1.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

### 12.2 Community Resources

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**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 12.3 Trademarks

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All other trademarks are the property of their respective owners.

### 12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS61162DYFFR	NRND	DSBGA	YFF	9	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	TPS 61162D	

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

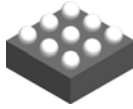
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS61162DYFFR	DSBGA	YFF	9	3000	180.0	8.4	1.45	1.45	0.8	4.0	8.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS61162DYFFR	DSBGA	YFF	9	3000	182.0	182.0	20.0

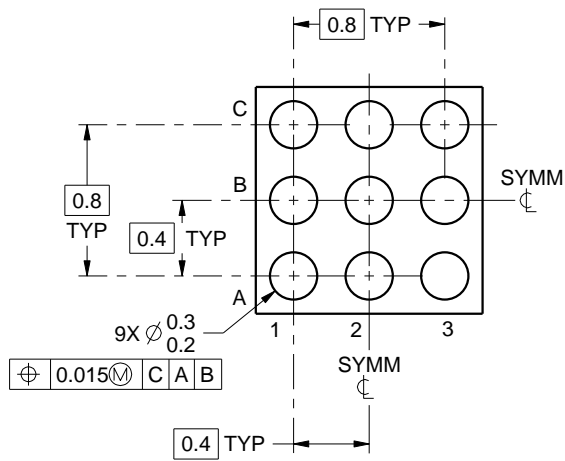
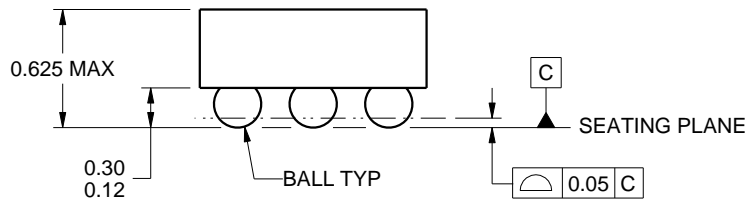
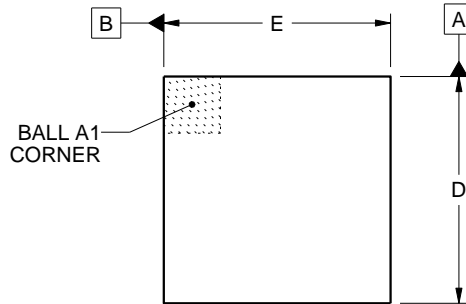
YFF0009



# PACKAGE OUTLINE

DSBGA - 0.625 mm max height

DIE SIZE BALL GRID ARRAY



D: Max = 1.336 mm, Min = 1.276 mm  
E: Max = 1.336 mm, Min = 1.276 mm

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NOTES:

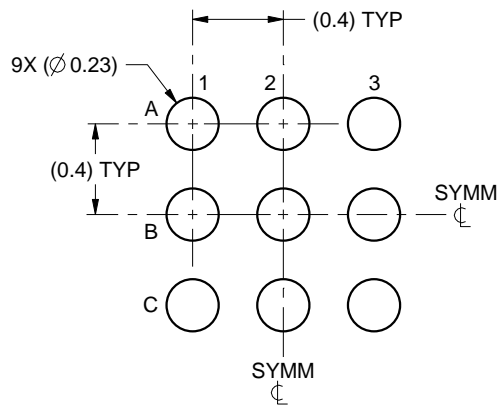
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

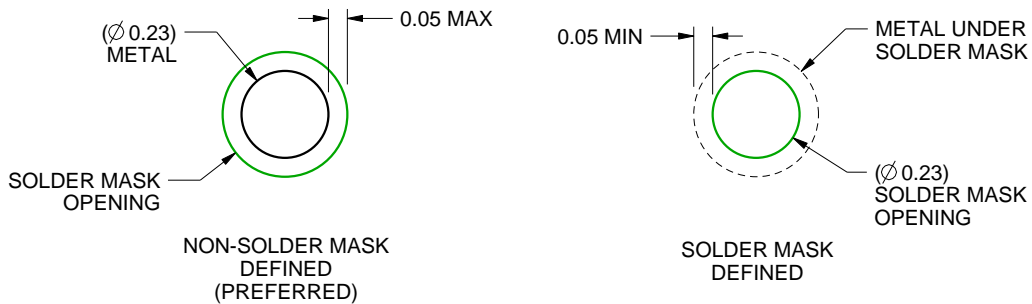
YFF0009

DSBGA - 0.625 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE  
SCALE:30X



SOLDER MASK DETAILS  
NOT TO SCALE

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NOTES: (continued)

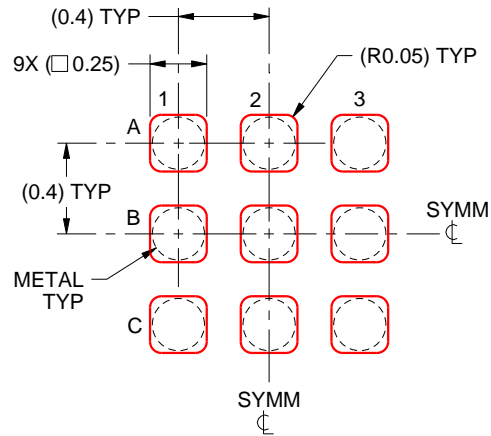
3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 ([www.ti.com/lit/snva009](http://www.ti.com/lit/snva009)).

# EXAMPLE STENCIL DESIGN

YFF0009

DSBGA - 0.625 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE  
BASED ON 0.1 mm THICK STENCIL  
SCALE:30X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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